



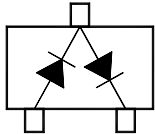
# 1SS226 Silicon Epitaxial Planar Switching Diode

## Features

- Glass Passivated Chip Junction
- Low forward voltage
- Fast reverse recovery time

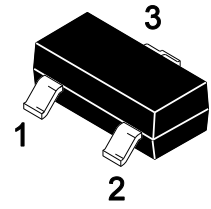
## Equivalent Circuit

3.Cathode1、 Anode2



1.Anode1 2.Cathode2

## SOT-23



1.Anode1 2.Cathode2  
3.Cathode1、 Anode2

Marking Code : B2

## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ )

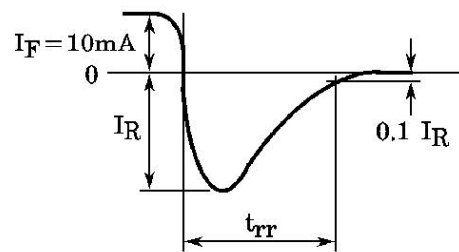
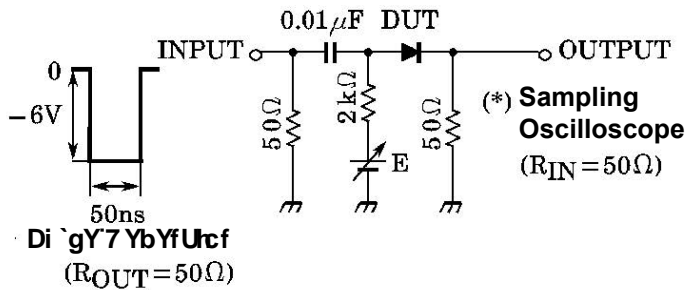
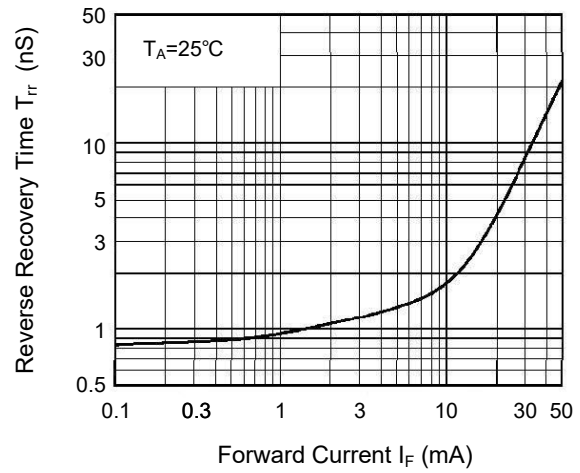
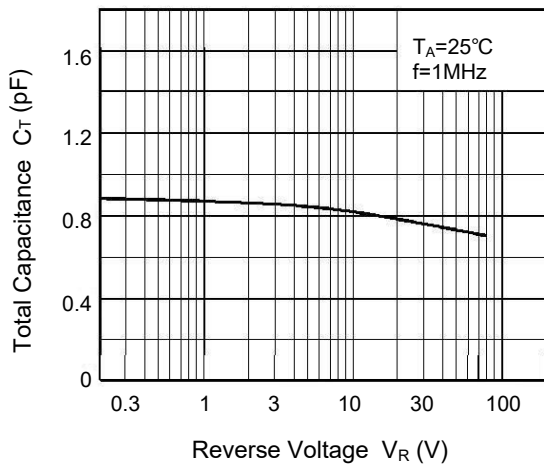
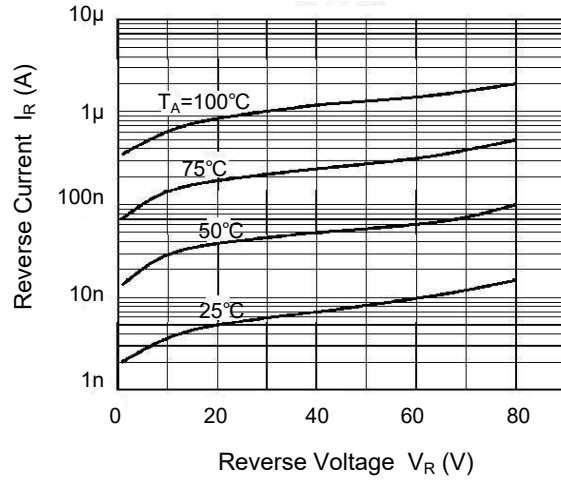
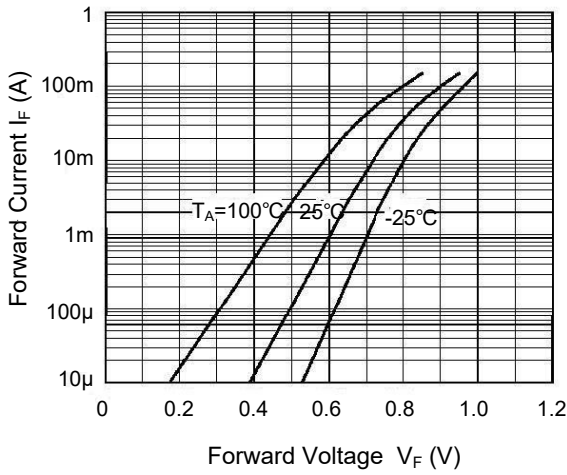
Parameter	Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	85	V
Reverse Voltage	$V_R$	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	$I_{FM}$	300	mA
Non-Repetitive Peak Forward Surge Current at $t=10\text{ms}$	$I_{FSM}$	2	A
Maximum Power Dissipation	$P_D$	350	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-50 to +150	$^\circ\text{C}$

## Electrical Characteristics ( $T_A=25^\circ\text{C}$ )

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	$V_F$	--	1.2	V
Reverse Current at $V_R = 80\text{ V}$	$I_R$	--	0.5	$\mu\text{A}$
Typical Junction Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_j$	--	3	pF
Maximum Reverse Recovery Time at $I_F = 10\text{ mA}$	$T_{rr}$	--	4	nS



### Typical Characteristic Curves



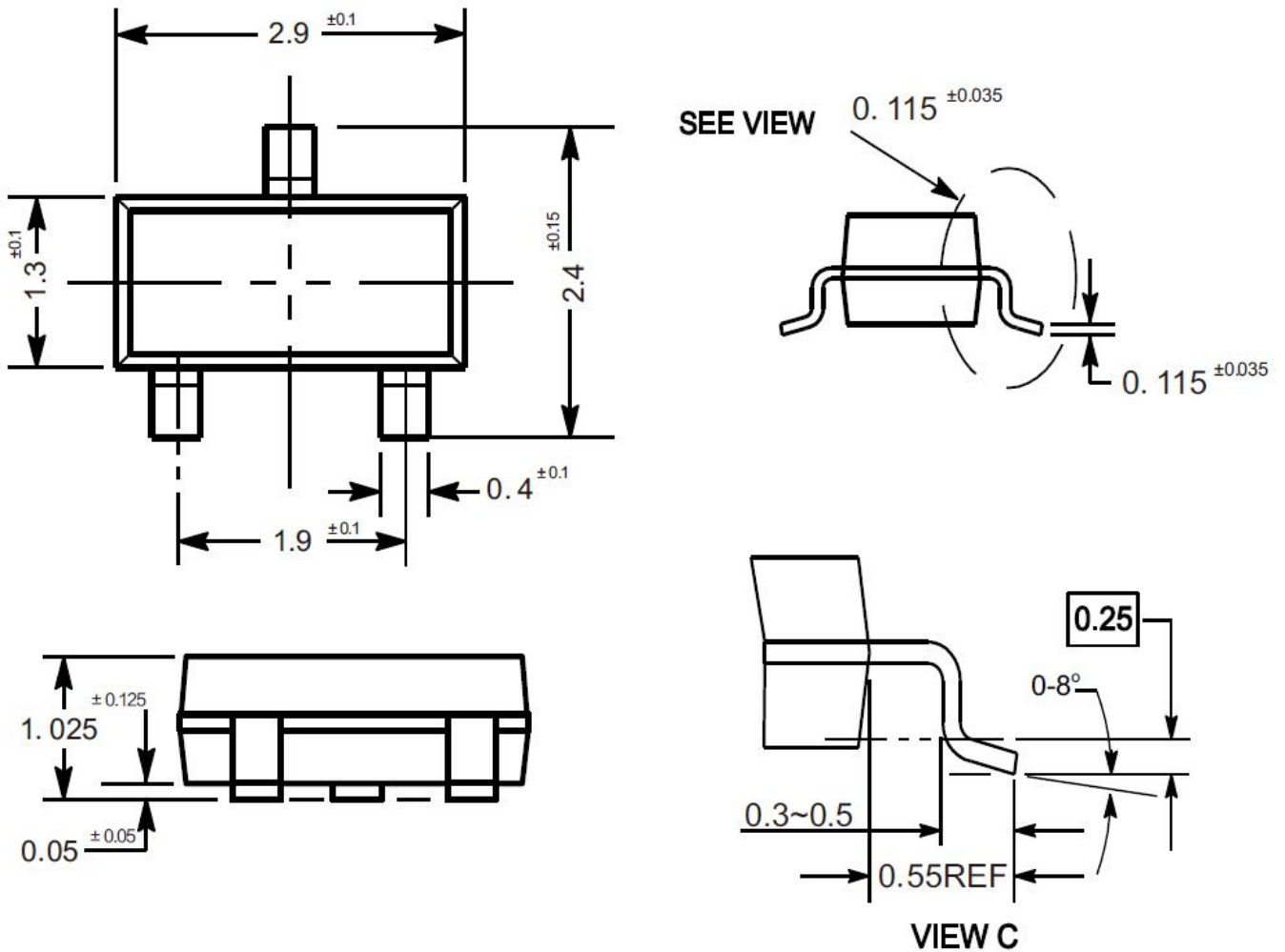


# 1SS226 Silicon Epitaxial Planar Switching Diode

## Package Outline

SOT-23

Dimensions in mm



## Ordering Information

Device	Package	Shipping
1SS226	SOT-23	3,000PCS/Reel&7inches